

Interfacial doping in $\text{LaVO}_3/\text{SrVO}_3$ multilayers from DFT+DMFT

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We investigate the effect of spatial doping of the Mott insulator LaVO_3 by inserting a few layers of the correlated metal SrVO_3 in multilayer geometries. Using density functional theory in combination with dynamical mean-field theory, we demonstrate that this leads to a geometrically confined and robust metallic layer that stabilizes the metallicity in SrVO_3 even in the ultrathin layer limit, suppressing a potential dimensionality-induced metal-insulator transition. For a thicker SrVO_3 layer, we find a continuous transition of both structural and electronic properties across the interface between the two materials, with bulk properties reestablished on a length scale of 2–3 unit cells away from the interface. We show that a strain modulation applied along the growth direction can lead to asymmetric charge reconstruction at chemically symmetric interfaces. However, we find that this effect is rather weak, implying that fractional occupancy, and thus metallicity, persists at the interfaces.

I. INTRODUCTION

Heterostructures constructed from complex oxides show great potential for novel electronic applications due to a variety of possible interfacial reconstruction effects [1–4]. Many of these systems show properties fundamentally different from those of the corresponding bulk compounds. Prominent examples are the quasi-two-dimensional electron gas and the interfacial magnetism emerging in between the otherwise non-magnetic band insulators LaAlO_3 and SrTiO_3 [5, 6].

The phenomenon of emerging phases is also present in simple solid solutions, where the gradual increase in cation substitution often leads to a transition region exhibiting properties that differ fundamentally from those of the two end compounds. One example is $\text{La}_{1-x}\text{Sr}_x\text{VO}_3$, where gradual changes of structural, spin, charge, and orbital degrees of freedom as a function of composition result in a transition to an antiferromagnetic metallic phase for $0.178 \leq x \leq 0.260$ [7] that is not present in either of the constituent compounds, with LaVO_3 being an antiferromagnetic Mott insulator and SrVO_3 a correlated metal.

On the other hand, whereas emerging properties in solid solutions are solely governed by the overall composition, artificial superlattices offer the spatial distribution as an additional powerful tuning parameter, allowing, e.g., for geometrically confined doping or variations in the individual layer thicknesses and periodicity. For example, an experimental study on $(\text{LaVO}_3)_m/(\text{SrVO}_3)_1$ superlattices reported a filling-controlled insulator-to-metal transition upon reducing $m \leq 4$, corresponding to a doping concentration of $x = 0.2$ [8]. However, a follow-up study then reported consistently metallic behavior for samples from $m = 2$ to $m = 6$ based on in-plane transport measurements, and it was suggested that pressure during

sample preparation may play an important role [9]. Interestingly, the same multilayers exhibited an insulating out-of-plane resistance, in contrast to the in-plane measurements, demonstrating the more complex properties emerging in superlattices compared to simple solid solutions.

Furthermore, the SrVO_3 layers buried in LaVO_3 do not show a dimensionality-induced metal-insulator transition (MIT), as reported, e.g., for ultra-thin films of SrVO_3 grown on SrTiO_3 [10, 11] and also for many other correlated metals. Such a transition generally results from the reduced bandwidth and orbital splittings due to symmetry lowering [11–16]. Instead, the dimensional crossover of an ultra-thin SrVO_3 film (3 unit cells) buried within LaVO_3 layers results in a weakly localized two-dimensional electron liquid state [17], promoting the idea of SrVO_3 acting as a geometrically confined dopant within LaVO_3 [9].

This picture is also supported by optical spectroscopy on $(\text{LaVO}_3)_{6n}/(\text{SrVO}_3)_n$ superlattices [18], for which valence changes differing from the nominal $3d^2$ and $3d^1$ valence in LaVO_3 and SrVO_3 , respectively, were observed using STEM-EELS measurements [19]. Although details could not be inferred at that time due to limited spatial resolution, a follow-up study investigated the valence states in $(\text{LaVO}_3)_6/(\text{SrVO}_3)_3$ superlattices more closely and with atomic resolution, showing an asymmetric charge distribution at chemically symmetric interfaces, which was suggested to result from an asymmetry in the out-of-plane lattice parameter due to strain relaxation [20]. The same study further revealed clear signatures of the mixed valence in the superlattice and a length scale for electronic reconstruction of 0.5–1.2 nm, in accordance with previous studies on related complex oxides [3, 21, 22].

A theoretical study on $(\text{LaVO}_3)_m/(\text{SrVO}_3)_1$ with $m = 5, 6$ used density functional theory (DFT)+ U to show that the interfacial vanadium sites can also arrange in a checkerboard pattern of V^{3+} and V^{4+} [23]. While the theoretically predicted insulating behavior in these

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superlattices agrees with the earlier reports in Ref. [8] and also with results from optical measurements [18], a metallic character was observed in the resistivity measurements of Ref. [9], raising the issue of oxygen vacancies [24]. A charge ordered checkerboard arrangement of V^{3+} and V^{4+} sites has also been reported in an earlier DFT+ U study of short periodicity $(\text{LaVO}_3)_1/(\text{SrVO}_3)_1$ multilayers [25].

From this brief summary, it is clear that the $\text{LaVO}_3/\text{SrVO}_3$ system has attracted considerable attention due to the interesting range of physical properties of the two bulk compounds, which is further extended in artificial heterostructures with additional control parameters. However, a conclusive picture of the electronic structure at the interface has not yet emerged, and thus first-principles calculations are required to elucidate the mechanisms of interfacial reconstruction at the atomic level. Here, we investigate multilayers with varying thicknesses of the Mott insulator LaVO_3 and the correlated metal SrVO_3 with regard to structural and electronic reconstruction using a combination of DFT and dynamical mean-field theory (DMFT). We show that at the DFT level there is a gradual transition between the bulk crystal structures and that this trend is robust with variation of the multilayer thickness. We demonstrate that charge is indeed transferred from LaVO_3 to SrVO_3 , leaving the interfacial V layer in a +3.5 oxidation state, consistent with its mixed chemical environment, and with occupations decaying to nominal values on a length scale of 2–3 unit cells at the DFT level. The role of SrVO_3 as a dopant is discussed at the DMFT level, where we find persistent metallicity in the interfacial layer, even if increased correlations drive SrVO_3 into an insulating state. Finally, we also demonstrate that asymmetric strain relaxation at the interface can indeed induce a weak electronic asymmetry at chemically symmetric interfaces.

The paper is structured as follows: In section II we introduce the multilayer structures and the computational methods used in this work. Structural and electronic results comparing the different multilayers are discussed in section III. A summary is presented in section IV.

II. COMPUTATIONAL METHOD

A. Supercell construction

To analyze the interplay between interfacial doping and the film thickness of the materials, we consider multiple superlattices, where we vary the number of layers of each component. We consider periodic $(\text{LaVO}_3)_i/(\text{SrVO}_3)_j$ multilayers, i/j in shorthand notation, where i and j refer to the number of LaO and SrO sublayers, respectively. The layers are stacked along the [001] direction (z -axis of the superlattices), which is chosen parallel to the long orthorhombic axis of the bulk LaVO_3 $Pbnm$ unit cell. We note that in the literature the alternative [110] $Pbnm$ stacking direction is

also commonly used [26, 27], which is briefly discussed in Sec. III A.

The in-plane lattice parameters of the superlattices are fixed to the average of the pseudocubic lattice constants $a_{\text{cub}} = (a/\sqrt{2} + b/\sqrt{2} + c/2)/3$ calculated for the two bulk materials; 3.894 Å for LaVO_3 and 3.859 Å for SrVO_3 , resulting in an average value of 3.877 Å. This corresponds to a moderate lattice mismatch of $\pm 0.45\%$, i.e., a small compressive and tensile strain for LaVO_3 and SrVO_3 , respectively. Thus, compared to experiment, the lattice mismatch is underestimated approximately by a factor of 2. While this could have a small quantitative effect on our results, we do not expect the qualitative picture to change. We further note that the specific strain levels in the experimental samples also depend on whether the superlattices are constrained to the substrate lattice constant or are (partially) relaxed.

All multilayers are constructed with $\sqrt{2} \times \sqrt{2}$ in-plane lattice vectors relative to the pseudocubic units to accommodate the tilts and rotations of the oxygen octahedra allowed within $Pbnm$ symmetry. We adopt the notation used in Refs. [16, 28] to quantify the octahedral tilt and rotation angles ϕ and θ (relative to the long orthorhombic c axis) in terms of specific bond angles depicted in Fig. 1. The tilt pattern in bulk LaVO_3 is $a^-a^-c^+$ in Glazer notation, whereas bulk SrVO_3 crystallizes in cubic $Pm\bar{3}m$ symmetry without octahedral tilts and rotations ($a^0a^0a^0$). In all multilayers presented here, a mirror plane parallel to the z -direction of the superlattices is preserved, which keeps B sites within the same xy -plane symmetry-equivalent. Since all B sites throughout the multilayer are occupied by the same atomic species, additional mirror planes perpendicular to the stacking direction are maintained in the central AO layers if both i and j are chosen to be odd numbers. This setup is used in all cases unless specified otherwise.

B. DFT + DMFT method

a. DFT calculation We use the QUANTUM ESPRESSO package [29] for the DFT calculations with the generalized gradient approximation of the exchange-correlation functional in the formulation of Perdew, Burke, and Ernzerhof (PBE) [30] and scalar-relativistic ultrasoft pseudopotentials. The $3s$ and $3p$ semicore states of V, the $4s$ and $4p$ semicore states of Sr, and the $5s$ and $5p$ semicore states of La, are treated as valence electrons, while the empty $\text{La-}4f$ states are not included. The plane-wave energy cutoffs are set to 70 Ry for the wavefunctions and to 840 Ry for the charge density. A Methfessel-Paxton scheme is used for the Brillouin-zone integration with a smearing parameter of 0.02 Ry. For the k -point sampling we use a $6 \times 6 \times 4$ Monkhorst-Pack grid for the smallest unit cell with $i = j = 1$ and a reduced number of points along k_z for all larger supercells. The atomic coordinates are relaxed until all force components are smaller than

1 mRy/ a_0 (a_0 : Bohr radius) and the energy difference in successive steps is below 0.1 Ry/ a_0 . The z component of the simulation cell is relaxed until the stress tensor component drops below 0.1 kbar, while both in-plane lattice parameters are kept fixed to the value given above. The effect of strain is addressed by adjusting the in-plane cell parameters accordingly and again relaxing the z -component.

b. DMFT calculation For the DMFT calculations we use a low-energy effective correlated subspace corresponding to the $V-t_{2g}$ -dominated bands. As in bulk LaVO_3 and SrVO_3 , the corresponding Kohn-Sham bands are well separated from lower $O-p$ dominated bands and have only minimal overlap with states higher in energy, here mostly $V-e_g$ dominated bands. The downfolding is performed using the WANNIER90 code [31], resulting in a set of three t_{2g} -like maximally localized Wannier functions per V site. We use TRIQS/solid_dmft [32] based on the TRIQS/DFTTools library [33] to run the DMFT cycle, where a self-consistent solution to the lattice problem is found when the local lattice Green's function matches that of the effective impurity problem. The local electron-electron interaction is parametrized in the Slater-Kanamori form, in terms of the inter-orbital Hubbard U and the Hund coupling J , including spin-flip and pair-hopping terms [34]. A double counting correction in the fully localized limit is subtracted [35, 36]. To solve the effective impurity problem, we use a continuous-time quantum Monte Carlo hybridization-expansion solver implemented in TRIQS/CTHYB [37] with inverse temperature $\beta = 1/(k_B T) = 40 \text{ eV}^{-1}$. To monitor the effect of the electron-electron interaction, we vary the Hubbard parameter U but fix the Hund's coupling to $J = 0.65 \text{ eV}$. The local occupations and the spectral weight at the Fermi level are calculated from the imaginary time Green's function as $n = -G(\beta)$ and $\tilde{A}(0) = -\frac{\beta}{\pi} \text{Tr}[G(\beta/2)]$, respectively. All results presented here are obtained from “one-shot” calculations, i.e., neglecting charge self-consistency.

III. RESULTS

A. Octahedral rotations

We first analyze how the distortion of the octahedral network evolves within the different superlattices. As already mentioned, bulk LaVO_3 exhibits octahedral tilts and rotations, while bulk SrVO_3 crystallizes in a perfect cubic structure. In Ref. [26] it was observed that for a constant number of LaVO_3 layers ($i = 6$), the octahedral tilt and rotation pattern in LaVO_3 remains bulk-like for a small number of SrVO_3 layers of up to $j < 5$. However, for more SrVO_3 layers, the experimental signal indicated complete suppression of tilts and rotations in LaVO_3 . In the following, we show that this trend cannot be observed in our calculations. Instead, we find that for all considered multilayers the tilt angles show a continuous tran-

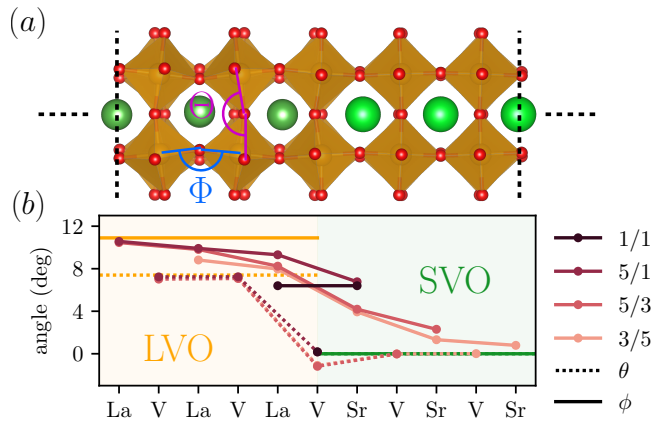


FIG. 1. (a) Unit cell of a 3/3 multilayer. La (Sr) atoms are shown in dark (bright) green, V in orange and O in red. From the TM-O-TM and O-O-O bond angles Φ and Θ , we define the octahedral tilt and rotation angles as $\phi = (\pi - \Phi)/2$ and $\theta = (\pi/2 - \Theta)/2$, illustrated by the blue and pink lines, respectively. (b) Evolution of octahedral tilts and rotations in the $\text{LaVO}_3/\text{SrVO}_3$ multilayers along the z direction, represented by solid and dashed lines, respectively. The corresponding strained bulk values are shown in orange for LaVO_3 and green for SrVO_3 .

sition across the interface over a length scale of 4 unit cells, whereas the rotation angles are nearly unaffected by the multilayer geometry and change abruptly at the interface.

Fig. 1(b) shows the layer-dependent tilt and rotation angles for a selected and representative number of superlattices. As a reference, the corresponding bulk values for LaVO_3 and SrVO_3 are indicated by the orange and green lines, respectively. We first discuss the evolution of the in-plane octahedral rotation angles θ , shown as dotted lines. For all multilayers, the rotation angles show a sharp transition from a finite value in LaVO_3 , essentially equal to the corresponding bulk value, to zero in SrVO_3 . An interesting observation is the absence of rotations in the interfacial VO_6 layer, suggesting that on the structural level the influence of the Sr environment dominates over that of La. In contrast, the tilt angles ϕ (solid lines) show a more continuous monotonic gradual reduction from the finite bulk value of LaVO_3 to zero inside the SrVO_3 layers. This transition occurs on a length scale of around 4 layers. Interestingly, the 1/1 superlattice essentially exhibits an $a^-a^-c^0$ tilt system (in Glazer notation).

In comparison to experiment, our results do not provide evidence for complete suppression of tilts for a larger number of SrVO_3 layers. It should be noted, however, that the growth direction in Ref. [26] was oriented along the orthorhombic [110] direction and thus differs from the setup used here. As reported in Ref. [27], the out-of-plane tilts in LaVO_3 are suppressed for this growth direction for a compressive strain above -3% . Although in the experiment the strain on LaVO_3 is only about -0.5 to -1% ,

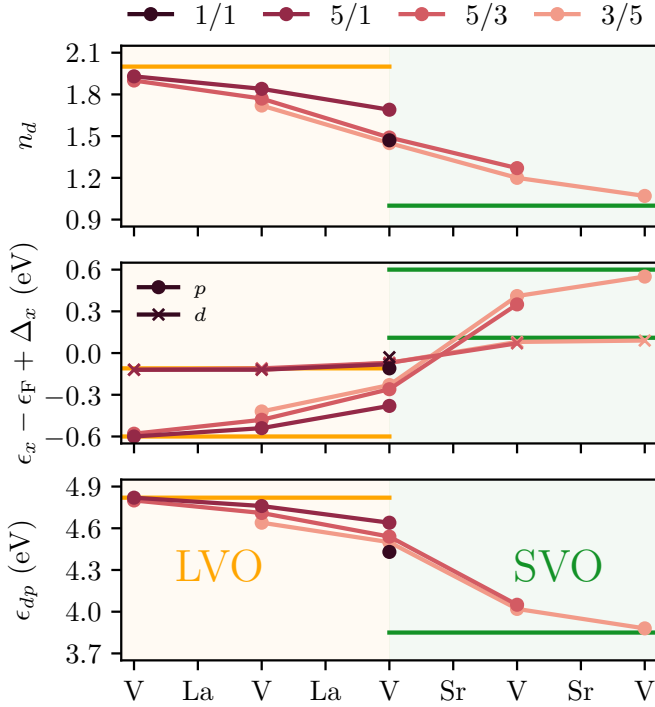


FIG. 2. Evolution of the changes in d occupation (top), the O- p , and TM- d (only t_{2g}) energies with respect to $\epsilon_F + \Delta_x$ ($x = p, d$), where ϵ_F is the Fermi level and $\Delta_p = 4.88$ eV and $\Delta_d = 0.54$ eV are arbitrary shifts introduced solely for better visualization on the same energy scale (middle), and the energy differences ϵ_{dp} (bottom) as a function of the TM site along the z direction of the multilayers.

other structural reconstruction mechanism such as cation intermixing or off-stoichiometry may have contributed to a suppression of octahedral tilts and rotations.

B. Electronic structure

Next, we discuss the interface-related changes in the electronic states on the basis of the DFT results. Fig. 2 shows the layer-dependent t_{2g} occupations, the charge transfer energy, $\epsilon_{dp} = \epsilon_d - \epsilon_p$, and the corresponding individual orbital energy levels for various multilayers with different thicknesses. Here, the occupations are computed from the layer-resolved density of states by integrating all atomic contributions per VO_2 layer over the energy region of the t_{2g} bands up to the Fermi level. To extract the energy levels corresponding to atomic-like p and d orbitals we construct a larger set of Wannier functions that includes the vanadium t_{2g} -derived states as well as the oxygen p states. The label d therefore refers to t_{2g} states only, while the energies of the ϵ_p are taken as the averaged Wannier levels of all oxygen p sites in the VO_2 layers.

We first focus on the evolution of the vanadium $3d$ occupations in the upper panel. Within the interfacial layer, the coordination of the vanadium is associated

equally with LaVO_3 or SrVO_3 on either side. As can be seen, this leads to a mixed oxidation state of $+3.5$, or an occupation of $1.5 e^-$, of the interfacial V cation, corresponding to the average over the two bulk compounds. The only exception occurs for a single dopant layer of SrO embedded in LaVO_3 (i.e., the 5/1 multilayer in Fig. 2), where the occupation in the interfacial layer is further increased towards the d^2 valence of LaVO_3 . Away from the interface, the occupations quickly converge to those in the corresponding bulk systems within about two layers, i.e., on a length scale very similar to that of the octahedral tilts discussed in Sec. III A. For all multilayers, the charge is consistently transferred from LaVO_3 to SrVO_3 , i.e., from the transition metal with a d^2 valence to that with a d^1 valence electron configuration, in accordance to earlier DFT+ U studies [25].

The direction of the charge transfer can be understood in terms of the occupancy difference of the d levels, as discussed in Ref. [38]. The average V oxidation state of $+3.5$ in the interfacial layer smooths the occupancy discontinuity between the nominal bulk oxidation states of the V sites, $+3$ and $+4$ for LaVO_3 and SrVO_3 , respectively. Furthermore, inspecting the evolution of the charge transfer energy, ϵ_{dp} (bottom panel of Fig. 2), which can be related to the electronegativity of the transition metal cations relative to the oxygen ligands, we find that the evolution of ϵ_{dp} across the interface essentially mirrors the changes in the occupancy. Away from the interface, the difference in ϵ_{dp} becomes identical to that of the two bulk compounds (shown as orange and green lines), which is of the order of 1.0 eV. The lower ϵ_{dp} in SrVO_3 relative to LaVO_3 indicates a higher electronegativity of the V^{4+} cation in SrVO_3 , consistent with the observed charge transfer.

The middle panel of Fig. 2 illustrates that the variation of ϵ_{dp} is mainly due to the difference in the oxygen p levels, $\Delta\epsilon_p \sim 1.2$ eV, between the two bulk values, while the difference of the V d levels reduces ϵ_{dp} by approximately 0.2 eV. We find a gradual deviation of oxygen p levels from the corresponding bulk values by up to 0.3 eV on either side of the interface, smoothing the transition of oxygen p levels across the interface. This is in line with the “oxygen continuity condition” proposed in Ref. 39, stating that the p states of the oxygen network tend to align continuously across the interface.

C. DMFT results

We now discuss the DMFT results for selected multilayers. The first question we address concerns the thickness dependence of electronic reconstruction within the LaVO_3 layers. For this, we analyze the layer-dependent spectral weight at the Fermi level, $\tilde{A}(0)$, as well as the layer-dependent t_{2g} occupations as function of the interaction strength, represented by the Hubbard U parameter.

In the 3/1 case, shown in Fig. 3(a), the multilayer con-

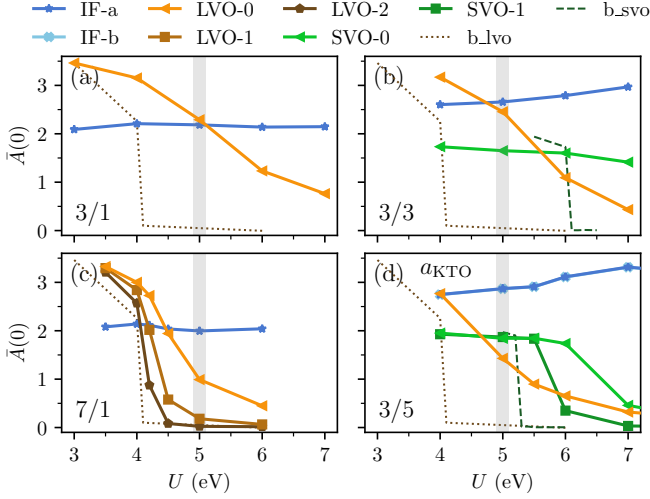


FIG. 3. Averaged spectral weight at the Fermi level, $\bar{A}(0)$, as a function of the interaction parameter U for different VO_2 layers in different multilayer geometries. Orange lines and symbols refer to LaVO_3 , while green ones represent SrVO_3 layers, with n in $\text{AVO}-n$ indicating the distance from the interface (and $A=L$ or S for LaVO_3 and SrVO_3 layers, respectively). Interface layers are denoted as IF (see main text for further details). The reference data for (unstrained) bulk LaVO_3 (b_{lvo}) and SrVO_3 (b_{svo}) are indicated by black dotted and dashed lines, respectively.

sists of four layers, with two symmetry-equivalent LaVO_3 layers with bulk coordination, denoted as LVO-0 and shown in orange, and two symmetry-equivalent interfacial VO_2 layers, shown in blue and labeled as IF- a . It can be seen that, for increasing U , the spectral weight at the Fermi level remains constant in the interfacial layer, while it is strongly decreased within the more bulk-like LaVO_3 layer. Simultaneously, the local electron-electron interaction establishes “nominal” occupations of approximately 2 and 1.5 in the LVO-0 and IF- a layers, respectively, for $U \approx 7 \text{ eV}$ (see Fig. 4(a)). Thus, for a typical interaction strength of $U \approx 5 \text{ eV}$ [27, 40, 41], all layers are metallic, and remain so up to at least $U = 7 \text{ eV}$.

Increasing the LaVO_3 layer thickness, as shown for the 7/1 multilayer in Fig. 3(c), reveals that already the second layer away from the interface, denoted as LVO-1, has only minimal remaining spectral weight at the Fermi level for $U = 5 \text{ eV}$, while the innermost layer, LVO-2, is essentially already bulk-like. Interestingly, even the first layer, LVO-0, is evidently more bulk-like (with strongly reduced spectral weight above $\sim 4 \text{ eV}$) compared to the corresponding layer in the 3/1 multilayer. This is a result of the transferred charge being redistributed over a larger number of LaVO_3 layers, which are thus closer to the nominal occupancy, as shown in Fig. 4(c). As for the 3/1 case, the metallic character of the interfacial VO_2 layer, IF- a , remains unaffected by changes in the interaction parameter. The metallicity of the interfacial layer seems to prevent the occupations to adopt exact integer values even for large U , in contrast to what has been observed,

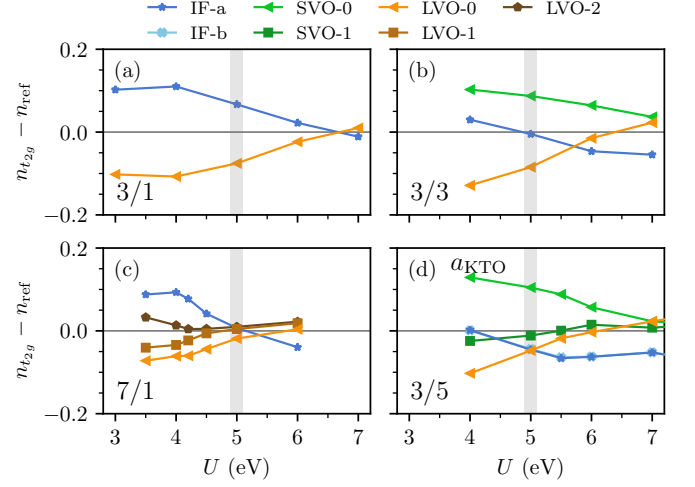


FIG. 4. Total t_{2g} occupation of symmetry-inequivalent VO_2 layers in different multilayers as a function of the interaction parameter U . For better visualization, all occupations are plotted relative to “reference occupations” n_{ref} , which are taken to be equal to 2 and 1 electrons for LaVO_3 and SrVO_3 layers, respectively, and equal to 1.5 for the interface layers (IF). The notation used to denote different layers is the same as in Fig. 3.

for example, from a similar analysis of charge transfer between two Mott insulators (see Fig. 4 in Ref. [42]). Interestingly, the small deviations from exact integer filling do not seem to disturb the Mott-insulating state within the LaVO_3 layers, as can be seen from the vanishing spectral weight of LVO-2 in Fig. 3(c) for large U , despite of its non-integer occupation.

From this we conclude that, despite the doping, bulk-like behavior is restored in LaVO_3 within 2–3 layers away from the interface. Thus, in contrast to Ref. [8], but consistent with the later reports in Ref. [9], our results show no indications of a filling-controlled insulator-to-metal transition for $m/1$ superlattices with $m \leq 4$. Even though the LaVO_3 layers further away from the interface become insulating, the 7/1 multilayer is still expected to have a conducting channel at the interface, which would lead to metallic in-plane conductivity. On the other hand, out-of-plane transport measurements would indeed be expected to exhibit insulating behavior for sufficiently thick LaVO_3 layers. Furthermore, comparing to the solid solution, the 7/1 multilayer would correspond to a doping concentration of $x = 0.125$ and would thus be expected to be a paramagnetic insulator at room temperature[43]. Our result thus further demonstrates the distinct behavior of heterostructures compared to solid solutions, thanks to the spatially coherent arrangement of the chemical constituents.

Next, we consider the effect of increasing the number of SrVO_3 layers, using the 3/3 multilayer as an example, shown in Fig. 3(b). While the behavior of the LaVO_3 layer remains unchanged compared to the 3/1 case, the additional SrVO_3 layer seems to enhance the metallic

regime at the interface and within the SrVO_3 layer. This is perhaps not surprising considering that SrVO_3 is a correlated metal with a finite quasiparticle weight for $U = 5\text{ eV}$. However, as indicated by the dashed dark green line in Fig. 3 (labeled b_svo), bulk SrVO_3 undergoes an MIT at $U_{\text{MIT}} \approx 6\text{ eV}$, while the single SrVO_3 layer in the 3/3 multilayer shows no such transition. This indicates that the charge reconstruction at the interface, extending into the adjacent LaVO_3 and SrVO_3 layers (see Fig. 4(b)), stabilizes the metallicity. Our results further confirm the absence of a dimensionality-induced metal-insulator transition reported for ultra-thin SrVO_3 films grown on SrTiO_3 [10, 11] when buried instead in LaVO_3 layers [17].

At this point, we briefly summarize that our DMFT results indicate that the interfacial layer is persistently metallic for all multilayers. While on the LaVO_3 side the Mott-insulating state and approximately nominal occupations are recovered on a length scale of 2-3 unit cells, the metallicity on the SrVO_3 side is enhanced compared to bulk SrVO_3 . The two questions we want to address next are (a) whether the thickness of the metallic layer can be tuned and (b) under what circumstances the two interfaces can be brought into a charge/interfacial ordered state with integer occupations that could promote a Mott-insulating state across all layers. We first focus on question (a), while (b) is discussed in Section III D.

To address the first question, we show in Fig. 3(d) a calculation for a strained superlattice of three layers of LaVO_3 and five layers of SrVO_3 (3/5 multilayer), where the in-plane pseudo-tetragonal lattice parameter is fixed to the bulk lattice constant of KTaO_3 . This choice is based on the fact that KTaO_3 , if chosen as a substrate, would impose a sufficiently large lattice mismatch with respect to SrVO_3 to result in an MIT [44]. For the experimental lattice constant of bulk KTaO_3 [45], $a_{\text{KTO}} = 3.981\text{ \AA}$, the tensile strain amounts to 2.2 % and 3.2 % in LaVO_3 and SrVO_3 , respectively. While this is not expected to lead to noticeable changes within LaVO_3 [44], a comparable magnitude of tensile strain shifts SrVO_3 towards the insulating regime [44], indicated by the calculated decrease of U_{MIT} from 6 eV to slightly above 5 eV in the strained bulk reference shown in Fig. 3(d).

As seen by the sudden decrease of spectral weight for $U \geq 5.5\text{ eV}$ in the SVO-1 layer, and at somewhat higher U also in the SVO-0 layer, the tensile strain indeed supports formation of the Mott-insulating phase in SrVO_3 also in the multilayer, similar to what has been found for the bulk case [44]. On the other hand, even in this case the interfacial layer, IF- a , remains persistently metallic, with a high spectral weight around the Fermi level, even for large U values. As expected, the LaVO_3 layer is only marginally affected by the tensile strain. The occupations in Fig. 4(d) again show a tendency towards integer bulk occupations under increasing U , without actually reaching exact integer values even for large interaction parameter. These results indicate that for large

tensile strain it might be possible to obtain insulating solutions on both sides of the interface, while the interface itself remains metallic, with the resulting metallicity being strongly two-dimensional, i.e., localized within a single VO_2 layer.

D. Strain-modulated multilayers

Ref. [20] reported an atomic scale oxidation map of $(\text{LaVO}_3)_6/(\text{SrVO}_3)_3$ superlattices via STEM-EELS measurements, revealing an electronic asymmetry in the valence configuration between the “upper” and “lower” $\text{LaVO}_3/\text{SrVO}_3$ interfaces (relative to the growth direction), despite the interfaces being chemically symmetric. The oxidation states of the interfacial VO_2 layers were found to range between the expected +3 in LaVO_3 and +4 in SrVO_3 , but were not identical at the two interfaces. This was associated with the observation of a local strain modulation along the z -direction of the superlattice. Consistent with the expected epitaxial strain, the cell parameters along the z direction of the films were found to vary by about +1.5 % within LaVO_3 and by -3 % within SrVO_3 with respect to the in-plane lattice constant fixed to the SrTiO_3 substrate. Interestingly, the modulation of the lattice parameter along the z direction showed an asymmetric profile, with a more abrupt change at one interface, and a more gradual change at the other. This was interpreted as a result of strain relaxation during the growth process [46].

Here, we explore the possibility of obtaining such an interfacial charge imbalance by imposing different strain modulations along the z -axis. As mentioned in the previous section, a strong interfacial asymmetry, leading to integer occupations of the interfacial V cations, could in principle allow for a global Mott insulating state in the multilayer. We note that an in-plane charge order within each interface, as explored with DFT+ U in Refs. [23, 25], provides an alternative route to a possible insulating state at the interface, which we do not pursue here.

Analogous to Ref. [20], we use a 6/3 multilayer, for which we consider three different strain profiles along the z -axis, as shown in Fig. 5(a): i) the fully relaxed case, ii) the experimental strain profile enhanced by a factor of five, and iii) a case with constant strain levels in the two components but asymmetric interfaces. Here, the strain in each VO_2 layer is defined as the distance between A (La/Sr) sites in the adjacent AO layers, relative to the fixed in-plane lattice constant.

The experimental strain profile is extracted from Fig. 1(b) of Ref. [20], averaged over three superlattice periods. The A site positions as well as the length of the simulation cell along z are then adjusted accordingly and kept fixed, while all other internal coordinates are relaxed. To potentially obtain a stronger effect of the strain modulation, the magnitude of the experimental strain distribution is enhanced by a factor of five. For the simplified case

valences at the interfaces, which would be required to obtain a Mott-insulating state for sufficiently strong interaction parameters. This further confirms the results presented in Section III C that the interface metallicity is very robust. Furthermore, imposing the experimentally measured strain profile in our calculations, even with strongly enhanced amplitude, does not reproduce the experimentally observed valence profile even qualitatively. This indicates that factors other than pure strain, such as, e.g., more complex structural relaxations, cation intermixing, the specific substrate orientation, defects, etc., are likely to be relevant.

IV. CONCLUSIONS

We investigated the structural and electronic reconstruction of multilayers consisting of the Mott insulator LaVO_3 and thin layers of the correlated metal SrVO_3 . For the [001] substrate orientation studied here, the octahedral tilts present in LaVO_3 penetrate slightly into the first few SrVO_3 layers, while the octahedral rotations around [001] drop to zero abruptly at the interface. In addition, there is electronic charge transfer from LaVO_3 towards SrVO_3 across the interface, with the V-cations in the interfacial layers assuming an intermediate oxidation state of $+3.5$, except for the case of a single SrO layer embedded within LaVO_3 , where the corresponding d -orbital occupation becomes larger than $1.5e^-$. Thus, the insertion of even a single layer of SrO into LaVO_3 leads to hole doping of the Mott insulator and a metallic layer that persists even for large interaction parameters,

even though a large U tends to drive the occupation towards integer values. Both on the structural and electronic level, we find that the length scale of reconstruction is of the order of two unit cells, which is consistent with earlier studies of similar systems [20, 21].

While a gap in the local spectral function is recovered in LaVO_3 layers away from the interface, the metallicity in SrVO_3 is stabilized. This indeed suggests a picture of geometrically confined doping [9] in buried layers of SrVO_3 , in contrast to the dimensionality-induced metal-insulator transition in ultra-thin films of SrTiO_3 [10]. Our results therefore highlights the importance of the spatial arrangement of the atoms in multilayer geometries compared to simple solid solutions with identical overall composition, which opens new possibilities for designing artificial functional materials.

We further demonstrated that an inhomogeneous strain modulation applied along the growth direction introduces additional charge reconstruction that can create electronically asymmetric interfaces. However, the effect is relatively weak and is therefore not sufficient to result in a Mott insulating state with integer occupations across all layers.

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- [1] J. Mannhart and D. G. Schlom, *Science* **327**, 1607 (2010).
 - [2] P. Zubko, S. Gariglio, M. Gabay, P. Ghosez, and J.-M. Triscone, *Annu. Rev. Condens. Matter Phys.* **2**, 141 (2011).
 - [3] H. Y. Hwang, Y. Iwasa, M. Kawasaki, B. Keimer, N. Nagao, and Y. Tokura, *Nat. Mater.* **11**, 103 (2012).
 - [4] J. Chakhalian, A. Millis, and J. Rondinelli, *Nat. mater.* **11**, 92 (2012).
 - [5] A. Ohtomo and H. Hwang, *Nature* **427**, 423 (2004).
 - [6] A. Brinkman, M. Huijben, M. V. Zalk, J. Huijben, U. Zeitler, J. C. Maan, W. G. V. d. Wiel, G. Rijnders, D. H. A. Blank, and H. Hilgenkamp, *Nat. Mater.* **6**, 493 (2007).
 - [7] S. Miyasaka, T. Okuda, and Y. Tokura, *Phys. Rev. Lett.* **85**, 5388 (2000).
 - [8] W. C. Sheets, B. Mercey, and W. Prellier, *Applied Physics Letters* **91**, 192102 (2007).
 - [9] U. Lüders, W. C. Sheets, A. David, W. Prellier, and R. Frésard, *Phys. Rev. B* **80**, 241102 (2009).
 - [10] K. Yoshimatsu, T. Okabe, H. Kumigashira, S. Okamoto, S. Aizaki, A. Fujimori, and M. Oshima, *Phys. Rev. Lett.* **104**, 147601 (2010).
 - [11] Z. Zhong, M. Wallerberger, J. M. Tomczak, C. Taranto, N. Parragh, A. Toschi, G. Sangiovanni, and K. Held, *Phys. Rev. Lett.* **114**, 246401 (2015).
 - [12] R. Scherwitzl, S. Gariglio, M. Gabay, P. Zubko, M. Gibert, and J.-M. Triscone, *Phys. Rev. Lett.* **106**, 246403 (2011).
 - [13] M. Gu, J. Laverock, B. Chen, K. E. Smith, S. A. Wolf, and J. Lu, *J. Appl. Phys.* **113**, 133704 (2013).
 - [14] A. Biswas, K.-S. Kim, and Y. H. Jeong, *J. Appl. Phys.* **116**, 213704 (2014).
 - [15] Z. Liao, F. Li, P. Gao, L. Li, J. Guo, X. Pan, R. Jin, E. W. Plummer, and J. Zhang, *Phys. Rev. B* **92**, 125123 (2015).
 - [16] S. Beck, G. Schlauzero, U. Chopra, and C. Ederer, *Phys. Rev. B* **97**, 075107 (2018).
 - [17] Q.-R. Li, M. Major, M. B. Yazdi, W. Donner, V. H. Dao, B. Mercey, and U. Lüders, *Phys. Rev. B* **91**, 035420 (2015).
 - [18] D. W. Jeong, W. S. Choi, T. D. Kang, C. H. Sohn, A. David, H. Rotella, A. A. Sirenko, C. H. Lee, J. H. Kim, U. Lüders, W. Prellier, Y.-J. Kim, Y. S. Lee, and T. W. Noh, *Phys. Rev. B* **84**, 115132 (2011).
 - [19] P. Boullay, A. David, W. C. Sheets, U. Lüders, W. Prellier, H. Tan, J. Verbeeck, G. Van Tendeloo, C. Gatel, G. Vincze, and Z. Radi, *Phys. Rev. B* **83**, 125403 (2011).
 - [20] H. Tan, R. Egoavil, A. Béch , G. T. Martinez,

- S. Van Aert, J. Verbeeck, G. Van Tendeloo, H. Rotella, P. Boullay, A. Pautrat, and W. Prellier, *Physical Review B* **88**, 155123 (2013).
- [21] S. Okamoto and A. J. Millis, *Nature* **428**, 630 (2004).
- [22] C. Cantoni, J. Gazquez, F. Miletto Granozio, M. P. Oxley, M. Varela, A. R. Lupini, S. J. Pennycook, C. Aruta, U. S. di Uccio, P. Perna, and D. Maccariello, *Adv. Mater.* **24**, 3952 (2012), <https://onlinelibrary.wiley.com/doi/pdf/10.1002/adma.201200667>.
- [23] Q. Dai, U. Lüders, R. Frésard, U. Eckern, and U. Schwingenschlögl, *Adv. Mater. Interfaces* **5**, 1701169 (2018).
- [24] Q. Dai, U. Eckern, and U. Schwingenschlögl, *New J. Phys.* **20**, 073011 (2018).
- [25] S. Y. Park, A. Kumar, and K. M. Rabe, *Physical Review Letters* **118**, 087602 (2017).
- [26] U. Lüders, Q.-R. Li, R. Feyerherm, and E. Dudzik, *J. Phys. Chem. Solids* **75**, 1354 (2014).
- [27] G. Sclauzero and C. Ederer, *Phys. Rev. B* **92**, 235112 (2015).
- [28] J. M. Rondinelli and N. A. Spaldin, *Adv. Mater.* **23**, 3363 (2011).
- [29] P. Giannozzi, S. Baroni, N. Bonini, M. Calandra, R. Car, C. Cavazzoni, D. Ceresoli, G. L. Chiarotti, M. Cococcioni, I. Dabo, A. D. Corso, S. de Gironcoli, S. Fabris, G. Fratesi, R. Gebauer, U. Gerstmann, C. Gougoussis, A. Kokalj, M. Lazzeri, L. Martin-Samos, N. Marzari, F. Mauri, R. Mazzarello, S. Paolini, A. Pasquarello, L. Paulatto, C. Sbraccia, S. Scandalo, G. Sclauzero, A. P. Seitsonen, A. Smogunov, P. Umari, and R. Wentzcovitch, *Journal of Physics: Condensed Matter* **21**, 395502 (2009).
- [30] J. P. Perdew, K. Burke, and M. Ernzerhof, *Phys. Rev. Lett.* **77**, 3865 (1996).
- [31] A. A. Mostofi, J. R. Yates, Y.-S. Lee, I. Souza, D. Vanderbilt, and N. Marzari, *Comput. Phys. Commun.* **178**, 685 (2008).
- [32] M. E. Merkel, A. Carta, S. Beck, and A. Hampel, *Journal of Open Source Software* **7**, 4623 (2022).
- [33] M. Aichhorn, L. Pourovskii, P. Seth, V. Vildosola, M. Zingl, O. Peil, X. Deng, J. Mravlje, G. Kraberger, C. Martins, M. Ferrero, and O. Parcollet, *Comput. Phys. Commun.* **204**, 200 (2016).
- [34] C. Castellani, C. R. Natoli, and J. Ranninger, *Physical Review B* **18**, 4945 (1978).
- [35] I. V. Solov'yev, P. H. Dederichs, and V. I. Anisimov, *Phys. Rev. B* **50**, 16861 (1994).
- [36] V. I. Anisimov, F. Aryasetiawan, and A. I. Lichtenstein, *Journal of Physics: Condensed Matter* **9**, 767 (1997).
- [37] P. Seth, I. Krivenko, M. Ferrero, and O. Parcollet, *Comput. Phys. Commun.* **200**, 274 (2016).
- [38] H. Chen and A. Millis, *Journal of Physics: Condensed Matter* **29**, 243001 (2017).
- [39] Z. Zhong and P. Hansmann, *Physical Review X* **7**, 011023 (2017).
- [40] E. Pavarini, S. Biermann, A. Poteryaev, A. I. Lichtenstein, A. Georges, and O. K. Andersen, *Physical Review Letters* **92**, 176403 (2004).
- [41] M. De Raychaudhury, E. Pavarini, and O. K. Andersen, *Physical Review Letters* **99**, 126402 (2007).
- [42] S. Beck and C. Ederer, *Phys. Rev. Materials* **3**, 095001 (2019).
- [43] S. Miyasaka, Y. Okimoto, M. Iwama, and Y. Tokura, *Phys. Rev. B* **68**, 100406 (2003).
- [44] G. Sclauzero, K. Dymkowski, and C. Ederer, *Phys. Rev. B* **94**, 245109 (2016).
- [45] R. Wyckoff, *The Structure of Crystals: Supplement for 1930-1934 to the 2d ed*, American Chemical Society Monograph Series (Reinhold Publishing Corporation, 1935) p. 55.
- [46] J. Matthews and A. Blakeslee, *J. Cryst. Growth* **27**, 118 (1974).